NTST40120CT, NTSJ40120CTG, NTSB40120CT-1G, NTSB40120CTG, NTSB40120CTT4G

Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low $V_F = 0.43 \text{ V}$ at $I_F = 5 \text{ A}$

Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- Pb-Free and Halide-Free Packages are Available

Typical Applications

- Switching Power Supplies including Notebook/Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing Diodes
- Reverse Battery Protection
- Instrumentation

Mechanical Characteristics

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec

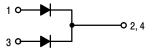


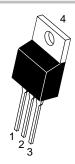
ON Semiconductor®

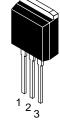
http://onsemi.com

VERY LOW FORWARD
VOLTAGE, LOW LEAKAGE
SCHOTTKY BARRIER
RECTIFIERS 40 AMPERES,
120 VOLTS

PIN CONNECTIONS







TO-220 CASE 221A STYLE 6

I²PAK CASE 418D STYLE 3





TO-220FP CASE 221AH

D²PAK CASE 418B

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

NTST40120CT, NTSJ40120CTG, NTSB40120CT-1G, NTSB40120CTG, NTSB40120CTT4G

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V _{RRM} V _{RWM} V _R	120	V
Average Rectified Forward Current (Rated V _R , T _C = 120°C)	Per Device Per Diode	I _{F(AV)}	40 20	А
Peak Repetitive Forward Current (Rated V _R , Square Wave, 20 kHz, T _C = 125°C)	Per Device Per Diode	I _{FRM}	80 40	А
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)		I _{FSM}	250	А
Operating Junction Temperature		TJ	-40 to +150	°C
Storage Temperature		T _{stg}	-40 to +150	°C
Voltage Rate of Change (Rated V _R)		dv/dt	10,000	V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Rating	Symbol	NTST40120CTG, NTSB40120CT-1G	NTSB40120CTG	NTSJ40120CTG	Unit
Maximum Thermal Resistance per Diode Junction–to–Case Junction–to–Ambient	$R_{ heta JC} \ R_{ heta JA}$	1.3 70	0.79 46.3	4.0 105	°C/W

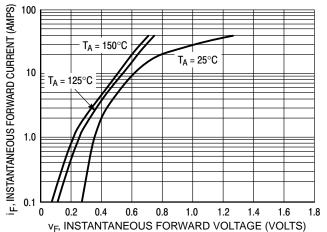
ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted)

Rating	Symbol	Тур	Max	Unit
Maximum Instantaneous Forward Voltage (Note 1)	٧ _F			V
$(I_F = 5 \text{ A}, T_J = 25^{\circ}\text{C})$		0.50	_	
$(I_F = 10 \text{ A}, T_J = 25^{\circ}\text{C})$		0.60	_	
$(I_F = 20 \text{ A}, T_J = 25^{\circ}\text{C})$		0.78	0.91	
$(I_F = 5 \text{ A}, T_J = 125^{\circ}\text{C})$		0.43	_	
$(I_F = 10 \text{ A}, T_J = 125^{\circ}\text{C})$		0.53	_	
$(I_F = 20 \text{ A}, T_J = 125^{\circ}\text{C})$		0.63	0.71	
Maximum Instantaneous Reverse Current (Note 1)	I _R			
$(V_R = 90 \text{ V}, T_J = 25^{\circ}\text{C})$		16	_	μΑ
$(V_R = 90 \text{ V}, T_J = 125^{\circ}\text{C})$		16	_	mA
(Rated dc Voltage, T _J = 25°C)		_	500	μΑ
(Rated dc Voltage, T _J = 125°C)		30	100	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 1. Pulse Test: Pulse Width = $300 \mu s$, Duty Cycle $\leq 2.0\%$

NTST40120CT, NTSJ40120CTG, NTSB40120CT-1G, NTSB40120CTG, NTSB40120CTT4G

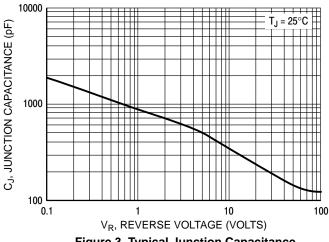
TYPICAL CHARACTERISITICS



100 T_A = 150°C 10 T_A = 125°C IR, REVERSE CURRENT (mA) 1.0 0.1 0.01 $T_A = 25^{\circ}C$ 0.001 30 110 20 70 80 90 100 120 V_R, REVERSE VOLTAGE (VOLTS)

Figure 1. Typical Forward Voltage

Figure 2. Typical Reverse Current



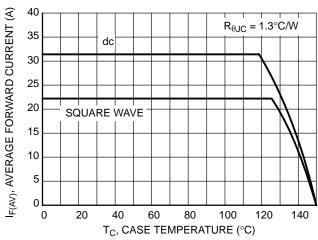
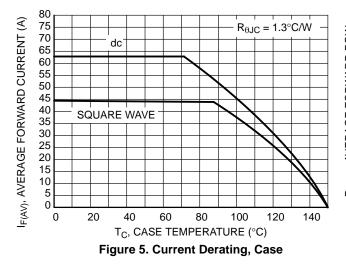


Figure 3. Typical Junction Capacitance

Figure 4. Current Derating per Leg



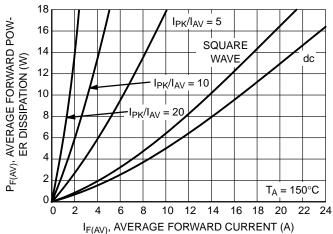


Figure 6. Forward Power Dissipation

NTST40120CT, NTSJ40120CTG, NTSB40120CT–1G, NTSB40120CTG, NTSB40120CTT4G

TYPICAL CHARACTERISITICS

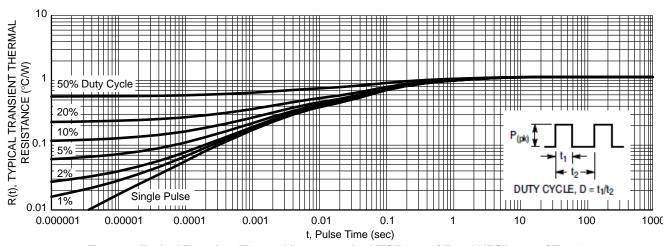


Figure 7. Typical Transient Thermal Response for NTST40120CT and NTSB40120CT-1G

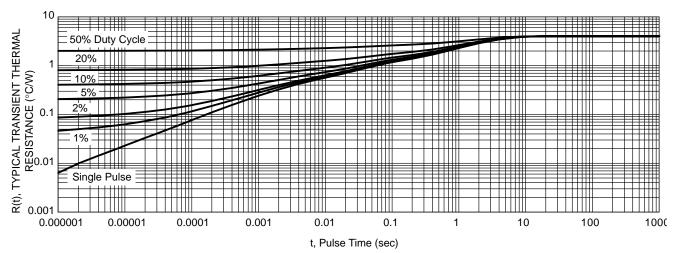


Figure 8. Typical Transient Thermal Response for NTSJ40120CTG

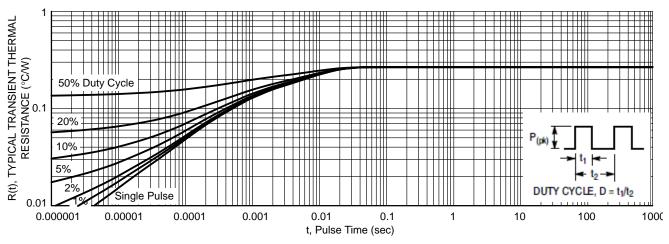


Figure 9. Typical Transient Thermal Response for NTSB40120CTG

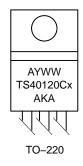
NTST40120CT, NTSJ40120CTG, NTSB40120CT-1G, NTSB40120CTG, NTSB40120CTT4G

ORDERING INFORMATION

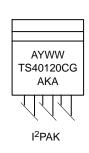
Device	Package	Shipping [†]
NTST40120CTG	TO-220 (Pb-Free)	50 Units / Rail
NTST40120CTH	TO-220 (Pb-Free and Halide-Free)	50 Units / Rail
NTSJ40120CTG	TO-220FP (Pb-Free and Halide-Free)	50 Units / Rail
NTSB40120CT-1G	l ² PAK (Pb-Free)	50 Units / Rail
NTSB40120CTG	D ² PAK (Pb-Free)	50 Units / Rail
NTSB40120CTT4G	D ² PAK (Pb-Free)	800 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MARKING DIAGRAMS









A = Assembly Location

Y = Year WW = Work Week

AKA = Polarity Designator

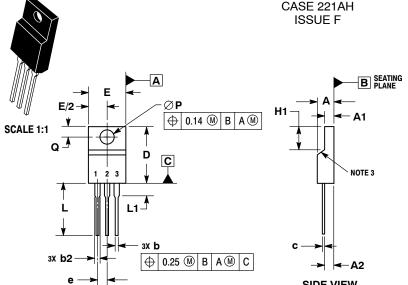
x = G or H

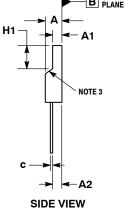
G = Pb-Free Package H = Halide-Free Package



TO-220 FULLPACK, 3-LEAD CASE 221AH

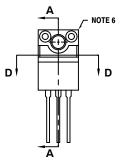
DATE 30 SEP 2014

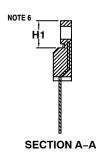






FRONT VIEW



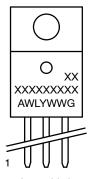


ALTERNATE CONSTRUCTION

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. CONTOUR UNCONTROLLED IN THIS AREA.
- CONTOUR ONCOUNTIOLLED IN THIS AREA
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE
 PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO
 EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEA SURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
 DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION.
 LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.
- CONTOURS AND FEATURES OF THE MOLDED PACKAGE BODY
 MAY VARY WITHIN THE ENVELOP DEFINED BY DIMENSIONS A1
 AND H1 FOR MANUFACTURING PURPOSES.

THE THE CIT WE THOUSE				
	MILLIMETERS			
DIM	MIN	MAX		
Α	4.30	4.70		
A1	2.50	2.90		
A2	2.50	2.90		
b	0.54	0.84		
b2	1.10	1.40		
С	0.49	0.79		
D	14.70	15.30		
E	9.70	10.30		
е	2.54	BSC		
H1	6.60	7.10		
L	12.50	14.73		
L1		2.80		
P	3.00	3.40		
Q	2.80	3.20		

GENERIC MARKING DIAGRAM*



= Assembly Location

WL = Wafer Lot

= Year

WW = Work Week

G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1:		STYLE 2:	
PIN 1.	MAIN TERMINAL 1	PIN 1.	CATHODE
2.	MAIN TERMINAL 2	2.	ANODE
3.	GATE	3.	GATE

DOCUMENT NUMBER:	98AON52577E	Electronic versions are uncontrolled except when accessed directly from the Document Rep Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	TO-220 FULLPACK, 3-LEAD		PAGE 1 OF 1

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves brisefin and of 160 m are trademarked so defined values of services and of the confined values and of the values of the confined values and of the values of the confined values and of the values of the v special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

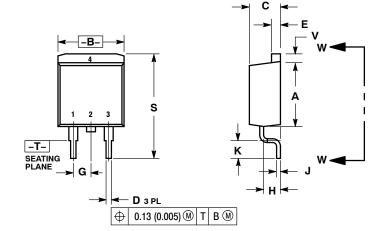




D²PAK 3 CASE 418B-04 **ISSUE L**

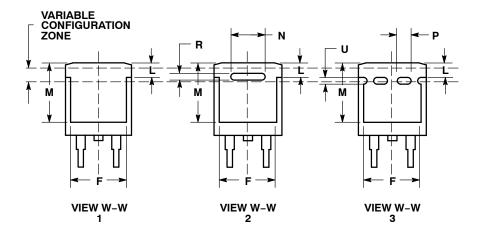
DATE 17 FEB 2015

SCALE 1:1



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
- 3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

	INCHES MILLIM		IETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.340	0.380	8.64	9.65
В	0.380	0.405	9.65	10.29
С	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54	BSC
Н	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197	0.197 REF		REF
P	0.079	REF	2.00 REF	
R	0.039	REF	0.99	REF
S	0.575	0.625	14.60	15.88
٧	0.045	0.055	1.14	1.40



STYLE 1: PIN 1. BASE 2. COLLECTOR
3. EMITTER
4. COLLECTOR STYLE 2: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN STYLE 3: PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE

STYLE 4:

PIN 1. GATE 2. COLLECTOR 3. EMITTER

4. COLLECTOR

STYLE 5:

PIN 1. CATHODE 2. ANODE 3. CATHODE 4. ANODE

STYLE 6:

PIN 1. NO CONNECT 2. CATHODE 3. ANODE 4. CATHODE

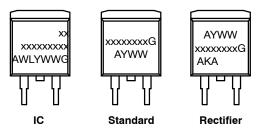
MARKING INFORMATION AND FOOTPRINT ON PAGE 2

DOCUMENT NUMBER:	98ASB42761B	Electronic versions are uncontrolled except when accessed directly from the Document Reportant Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	D ² PAK 3		PAGE 1 OF 2

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves brisefin and of 160 m are trademarked so defined values of services and of the confined values and of the values of the confined values and of the values of the confined values and of the values of the v special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

DATE 17 FEB 2015

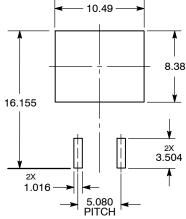
GENERIC MARKING DIAGRAM*



xx = Specific Device Code A = Assembly Location

WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb-Free Package
AKA = Polarity Indicator

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

DOCUMENT NUMBER:	98ASB42761B	Electronic versions are uncontrolled except when accessed directly from the Document Rep Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	D ² PAK 3		PAGE 2 OF 2

onsemi and ONSeMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.org/www.onsemi.or

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \underline{ www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales